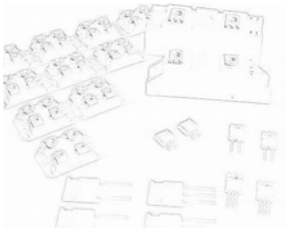
SIRECT
ELECTRONIC



Advantages from different barrier of Schottky

January 2007

1. Platinum (Pt) Barrier Schottky

(1) Extremely low Reverse Current Leakage (I_R) less than 10μA @ 25°C.

(2) High Operating Temperature (Tj) from 150°C. to 175°C.

(3) High Avalanche Level Ability.

(4) Good Electrostatic Discharge (ESD) Protection Capability from 8 to 12kv.

(5) Lower Electromagnetic Interference (EMI) effect on the high frequency application.

2. Molybdenum (Mo) Barrier Schottky

(1) Strong Electrostatic Discharge (ESD) Protection Capability from 15 to 35kv.

(2) High Operating Temperature (Tj) to 150°C

(3) Lower Electromagnetic Interference (EMI) effect on the high frequency application.

3. Chromium (Cr) Barrier Schottky

(1) Extremely Low Forward Voltage Drop (V_F) less than 0.38V @ 25°C

(2) Lower Electromagnetic Interference (EMI) effect on the high frequency application.

4. Alloy (Chromium+Nickle) Barrier Schottky

(1) Low Forward Voltage Drop (V_F) less than 0.35V @125°C

(2) Lower Electromagnetic Interference (EMI) effect on the high frequency application.

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